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View Online at https://aerobasegroup.com/nsn/5961-01-534-2313

view Online at https://aeiobasegioup.com/nsi//3901-01-334-2313	
Inclosure Material:	
Metal	
Overall Length:	
Between 1.124 inches and 1.308 inches	
End Application:	
Nsn 1140-01-087-9844; launching station, guided missile, semitrailer mouncter; w/s: missile, patroit	
Mounting Facility Quantity:	
1	
Internal Configuration:	
Junction contact	
Electrode Internally-electrically Connected To Case:	
Anode	
Mounting Method:	
Threaded stud	
Features Provided:	
Hermetically sealed case	
Overall Width Across Flats:	
Between 0.424 inches and 0.437 inches	
Thready Qty Per Inch (tpi):	
32	
Thread Size:	
0.190 inches	
Semiconductor Material:	
Silicon	
Voltage Rating In Volts Per Characteristic:	
600.0 repetitive peak off-state voltage and 600.0 repetitive peak reverse voltage	
Current Rating Per Characteristic:	
4.70 amperes forward current, total rms megahertz	
Maximum Operating Tempurature Per Measurement Point:	
150.0 degrees celsius ambient air	
Special Features:	
Junction pattern arrangement: pnpn	
Thread Series Designator:	
Unf	
Terminal Type And Quantity:	
2 tab, solder lug and 1 threaded stud	
Shelf Life:	
N/a	
Unit Of Measure:	
Demilitarization:	
No	

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